

LIST OF REFERENCES CITED BY APPLICANT Form PTO-1449 (Use several sheets if necessary)				ATTY. DOCKET NO.: 4717-7500		APPLICATION NO.: 10/615,259	
Sheet 1 of 1				APPLICANT: Bruno GHYSELEN et al.			
				FILING DATE: July 9, 2003		GROUP: 2818	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	B1	10-209453	08/1988	JP (Abstract)				

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)		
<i>TL</i>	C1	E.A. Fitzgerald et al. <i>Relaxed Ge_xSi_{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si</i> ; <u>J.Vac.Sci.Technol</u> ; B 10(4), Jul/Aug 1992; pp. 1807-1819.
<i>TL</i>	C2	R. Egloff et al. <i>Evaluation of Strain Sources in Bond and Etchback Silicon-on-Insulator</i> ; <u>Philips Journal of Research</u> ; Vol. 49, No. 1/2 1995; pp125-138.
<i>TL</i>	C3	Cher Ming Tan et al. <i>Temperature and Stress Distribution in the SOI Structure During Fabrication</i> ; <u>ZIEEE Transactions on Semiconductor Manufacturing</u> , Vol. 16, No. 2, May 2003; pp. 314-317.

EXAMINER <i>Therak</i>	DATE CONSIDERED <i>8/19/04</i>
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5/28/04

LIST OF REFERENCES CITED BY APPLICANT Form PTO-1449 <i>(Use several sheets if necessary)</i>		ATTY. DOCKET NO.: 4717-7500	APPLICATION NO.: 10/615,259
<div style="position: relative; height: 100px;"> <div style="position: absolute; top: 0; left: 0; width: 100%; height: 100%; border: 1px solid black; border-radius: 50%; text-align: center; color: black; font-weight: bold; font-size: 1.2em;"> O I P E J C I W MAY 28 2004 PATENT & TRADEMARK OFFICE </div> </div>		APPLICANT: Bruno GHYSELEN et al.	
		FILING DATE: July 9, 2003	
Sheet 1 of 1		GROUP: 2812	

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
R	A1	6,524,935	02/2003	Canaperi et al	438	478	/
	A2	2003/0089901	05/2003	Fitzgerald	257	19	
	A3	6,603,156	09/2003	Rim	257	190	
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							YES	NO
R	B1	2001168342	6/2001	JP			/	
	B2	WO 02/15244	02/2002	WO				
	B3	WO 02/27783	04/2002	WO				
	B4	WO 02/071493	09/2002	WO				
	B5	WO 02/080241	10/2002	WO				

OTHER REFERENCES *(Including Author, Title, Date, Pertinent Pages, Etc.)*

R	C1	Hobart, K.D. et al., <i>On Scaling the Thin Film Si Thickness of SOI Substrates, A Perspective on Wafer Bonding for Thin Film Devices</i> , Naval Research Laboratory, Electronics Science and Technology division Washington, DC 20375
R	C2	Mizuno, T. et al., <i>High Performance Strained-Si p-MOSFETs on SiGe-on-Insulator Substrates Fabricated by SIMO Technology</i> , Electron Devices Meeting , 1999. IEDM Technical Digest International, Washington, DC, USA 5-8 December 1999, Piscataway, NJ
R	C3	Tong, Q.Y. et al., <i>Semiconductor on Wafer Bonding</i> , Science and Technology, Interscience Technology, Johnson Wiley & Sons, Inc.

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